

描述 / Descriptions

SOP-8 塑封封装互补增强模式 MOS 场效应管。

Complementary Enhancement MOSFET in a SOP-8 Plastic Package.

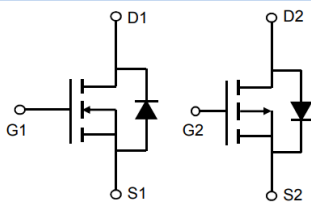
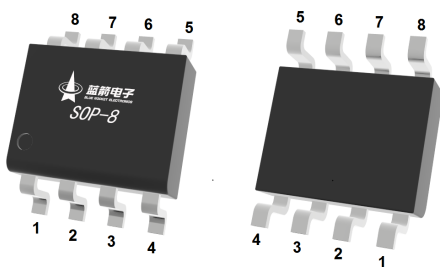
特征 / Features

N-channel	P-channel
$V_{DS}(V)=40V$	$V_{DS}(V)=-40V$
$I_D=8A(T_C=25^{\circ}C)$	$I_D=-7A(T_C=25^{\circ}C)$
$R_{DS(ON)}<25m\Omega(V_{GS}=10V)$	$R_{DS(ON)}<35m\Omega(V_{GS}=-10V)$
$R_{DS(ON)}<45m\Omega(V_{GS}=4.5V)$	$R_{DS(ON)}<60m\Omega(V_{GS}=-4.5V)$
无卤产品。HF Product.	

用途 / Applications

用于高功率 DC/DC 转换和功率开关。适用于作负载开关或脉宽调制应用。

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies. And suitable for use as a load switch or in PWM applications.

内部等效电路 / Equivalent Circuit**引脚排列 / Pinning**

PIN 1 : S1 PIN 2 : G1 PIN 3 : S2 PIN 4 : G2
 PIN 5 : D2 PIN 6 : D2 PIN 7 : D1 PIN 8 : D1

印章代码 / Marking

见印章说明。

See Marking Instructions.

极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating		单位 Unit
		N-channel	P-channel	
Drain-Source Voltage	V_{DSS}	40	-40	V
Gate-Source Voltage	V_{GSS}	± 20		V
Continuous Drain Current	$I_D (T_C=25^\circ\text{C})$	8	-7	A
Continuous Drain Current	$I_D (T_A=25^\circ\text{C})$	6	-5	A
Pulsed Drain Current	I_{DM}	20	-20	A
Power Dissipation	$P_D (T_C=25^\circ\text{C})$	3.5	3.5	W
Power Dissipation	$P_D (T_A=25^\circ\text{C})$	2	2	W
Maximum Junction-to-Ambient	$R_{\theta JA}$	$t \leq 10\text{s}$	62.5	$^\circ\text{C/W}$
	$R_{\theta JA}$	Steady-State	110	$^\circ\text{C/W}$
Maximum Junction-to-Case	$R_{\theta JC}$	Steady-State	35.7	$^\circ\text{C/W}$
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150		$^\circ\text{C}$

N-沟道电性能参数/N-CHANNEL Electrical Characteristics(Ta=25℃)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	40	44		V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V V _{GS} =0V			1.0	μA
		V _{DS} =40V V _{GS} =0V T _J =55℃			5.0	μA
Gate-Body leakage current	I _{GSS}	V _{GS} =±20V V _{DS} =0V			100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} I _D =250μA	1.4	1.6	3.0	V
On state drain current	I _{D(on)}	V _{DS} =10V V _{GS} =5.0V	20			A
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V I _D =6A		17.5	25	mΩ
		V _{GS} =4.5V I _D =5.0A		22.8	45	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5.0V I _D =6.0A		14		S
Diode Forward Voltage	V _{SD}	V _{GS} =0V I _S =1.0A		0.73	1.0	V
Input Capacitance	C _{iss}	V _{DS} =25V V _{GS} =0V f=1.0MHz		1200		pF
Output Capacitance	C _{oss}			310		pF
Reverse Transfer Capacitance	C _{rss}			65		pF
Gate resistance	R _g	V _{DS} =0V V _{GS} =0V f=1.0MHz		9.5		Ω
Total Gate Charge(10V)	Q _g	V _{GS} =10V V _{DS} =20V I _D =6A		8.3		nC
Total Gate Charge(4.5V)				4.2		nC
Gate-Source Charge	Q _{gs}			1.3		nC
Gate-Drain Charge	Q _{gd}			2.3		nC
Turn-On Delay Time	t _{d(on)}	V _{DS} =20 V V _{GS} =10V R _L =3.3Ω R _{GEN} =3Ω		4.2		ns
Turn-On Rise Time	t _r			3.3		ns
Turn-Off Delay Time	t _{d(off)}			15.6		ns
Turn-Off Fall Time	t _f			3		ns

N-沟道电参数曲线图 / N-CHANNEL Electrical Characteristic Curve

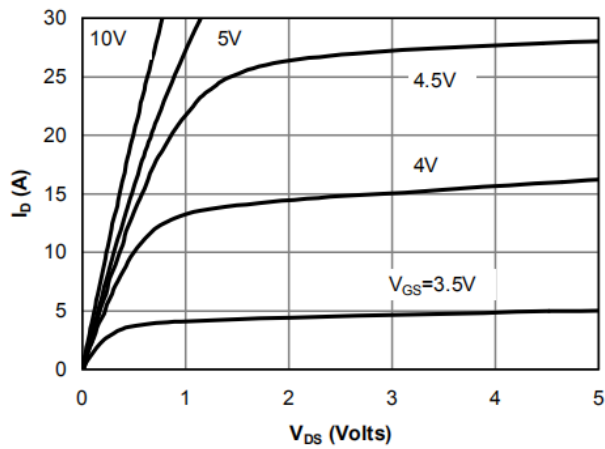


Fig 1: On-Region Characteristics

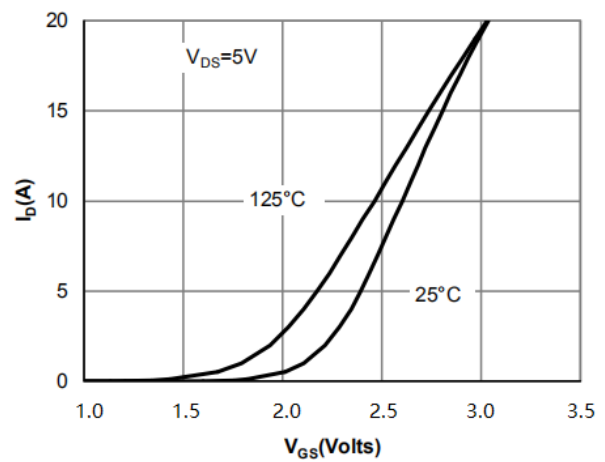


Figure 2: Transfer Characteristics

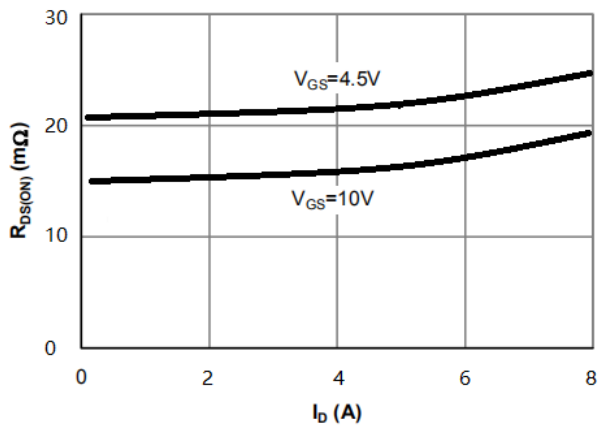


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

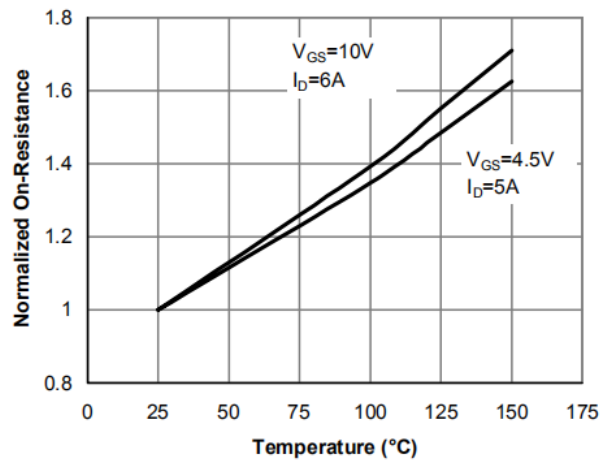


Figure 4: On-Resistance vs. Junction Temperature

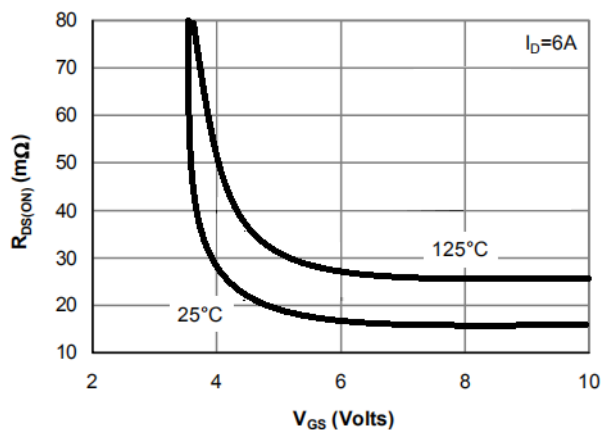


Figure 5: On-Resistance vs. Gate-Source Voltage

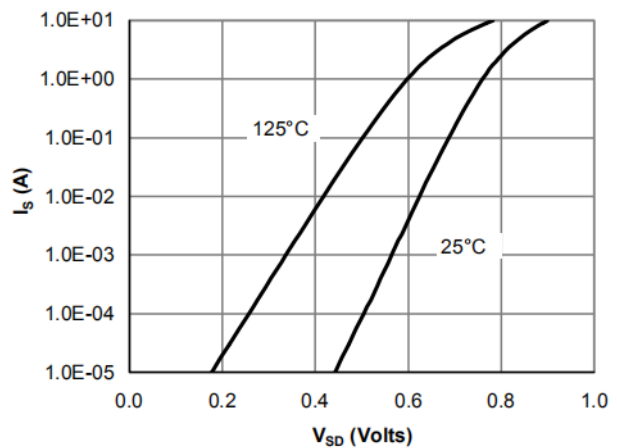
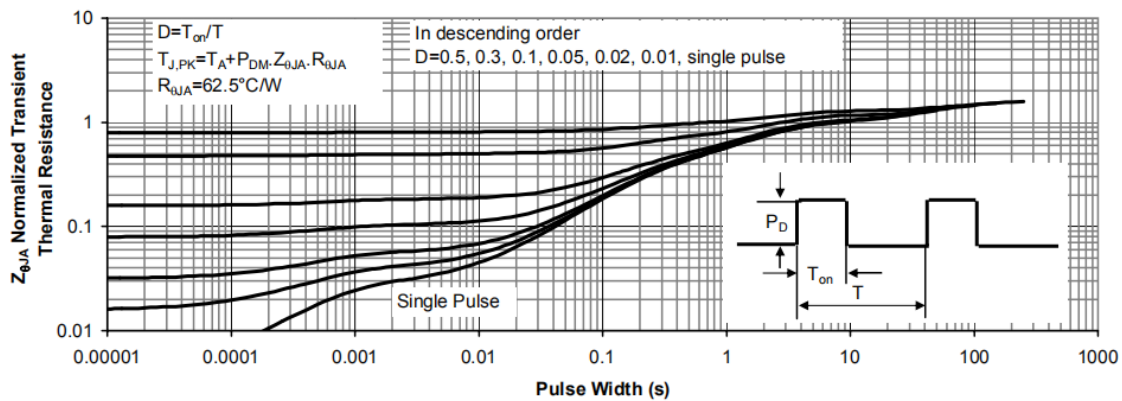
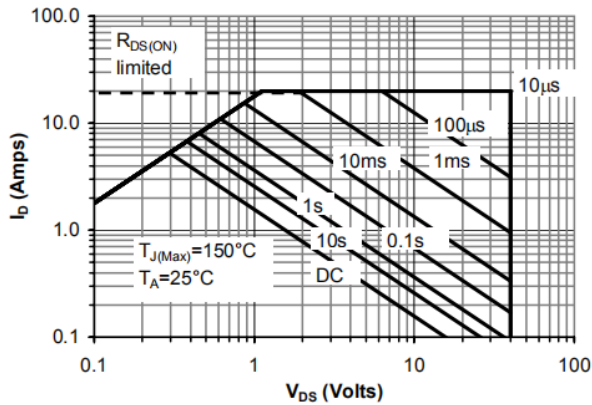
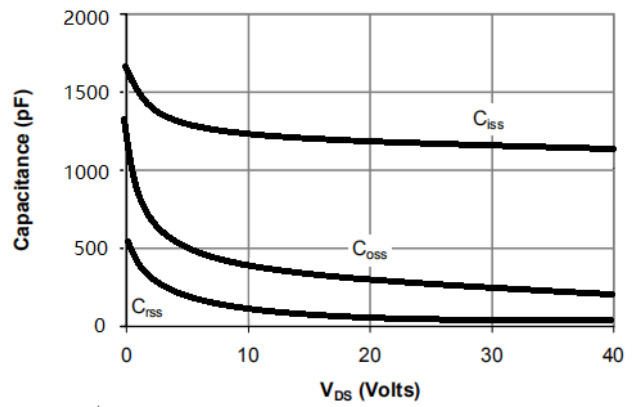
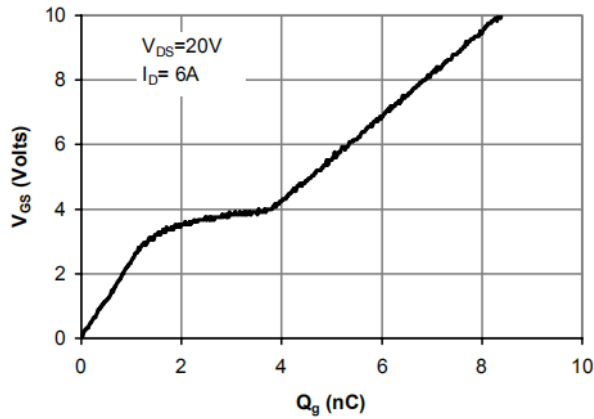


Figure 6: Body-Diode Characteristics

N-沟道电参数曲线图 / N-CHANNEL Electrical Characteristic Curve



P-沟道电性能参数/P-CHANNEL Electrical Characteristics(Ta=25℃)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-40	-46		V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-40V V _{GS} =0V			-1.0	μA
		V _{DS} =-40V V _{GS} =0V T _J =55℃			-5.0	μA
Gate-Body leakage current	I _{GSS}	V _{GS} =±20V V _{DS} =0V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} I _D =-250μA	-1.4	-1.6	-3.0	V
On state drain current	I _{D(on)}	V _{DS} =-5V V _{GS} =-10V	6			A
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-10V I _D =-5.0A		32	35	mΩ
		V _{GS} =-4.5V I _D =-2.0A		49	60	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-5.0V I _D =-4.8A		13		S
Diode Forward Voltage	V _{SD}	V _{GS} =0V I _S =-1.0A		-0.76	-1.0	V
Input Capacitance	C _{iss}	V _{DS} =-25V V _{GS} =0V f=1.0MHz		710		pF
Output Capacitance	C _{oss}			61		pF
Reverse Transfer Capacitance	C _{rss}			14		pF
Gate resistance	R _g	V _{DS} =0V V _{GS} =0V f=1.0MHz		2.1		Ω
Total Gate Charge(10V)	Q _g	V _{GS} =-10V V _{DS} =-20V I _D =-5.0A		13.6		nC
Total Gate Charge(4.5V)				6.8		nC
Gate-Source Charge	Q _{gs}			1.8		nC
Gate-Drain Charge	Q _{gd}			3.9		nC
Turn-On Delay Time	t _{d(on)}	V _{DS} =-20V V _{GS} =-10V R _L =4Ω R _{GEN} =3Ω		7.5		ns
Turn-On Rise Time	t _r			6.7		ns
Turn-Off Delay Time	t _{d(off)}			26		ns
Turn-Off Fall Time	t _f			11.2		ns

P-沟道电参数曲线图 / P-CHANNEL Electrical Characteristic Curve

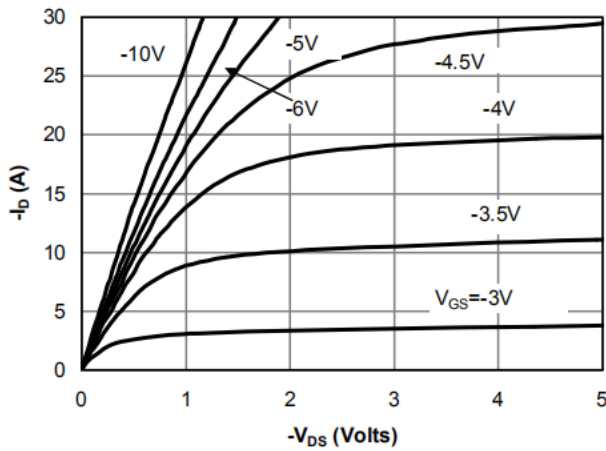


Fig 1: On-Region Characteristics

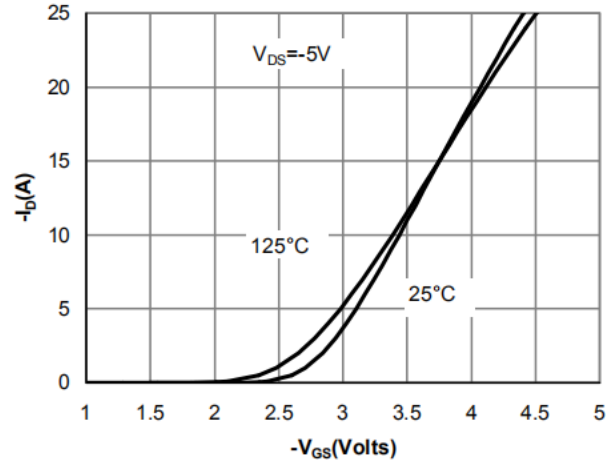


Figure 2: Transfer Characteristics

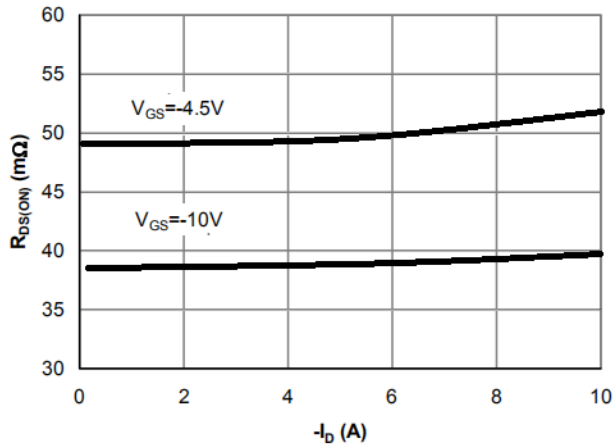


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

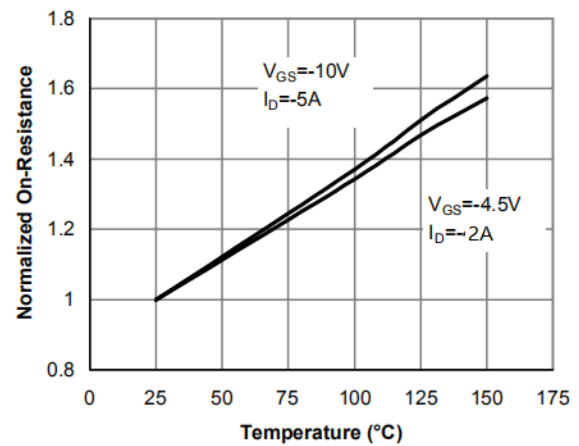


Figure 4: On-Resistance vs. Junction Temperature

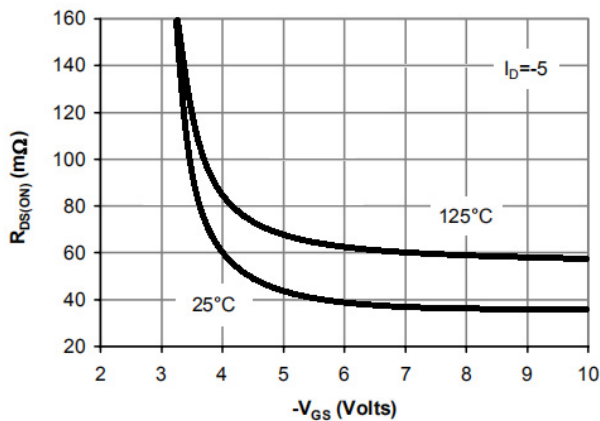


Figure 5: On-Resistance vs. Gate-Source Voltage

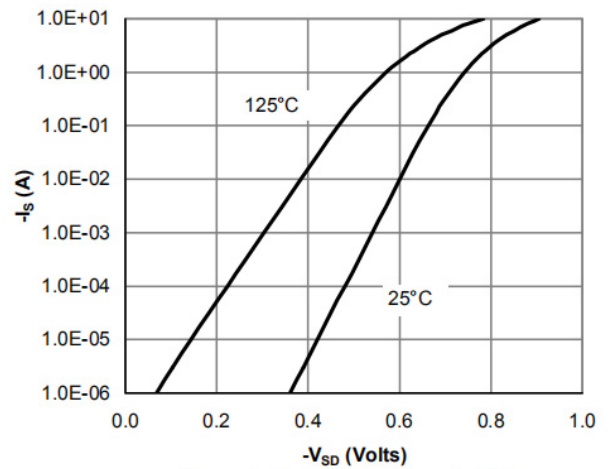


Figure 6: Body-Diode Characteristics

P-沟道电参数曲线图 / P-CHANNEL Electrical Characteristic Curve

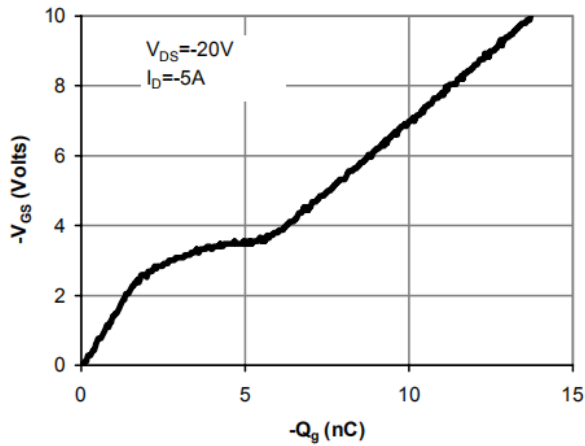


Figure 7: Gate-Charge Characteristics

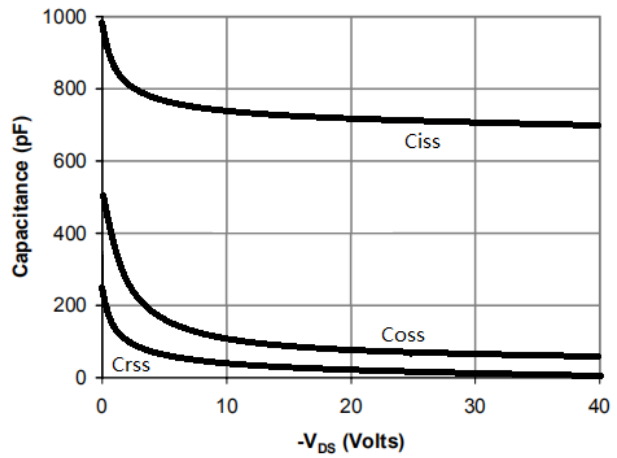


Figure 8: Capacitance Characteristics

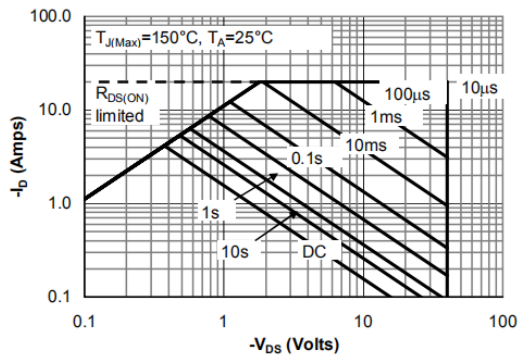


Figure 9: Maximum Forward Biased Safe Operating Area

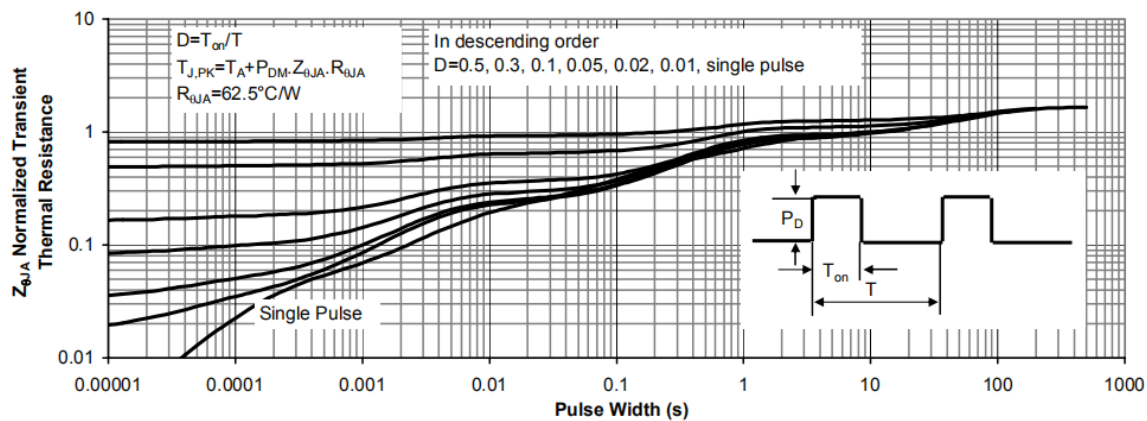
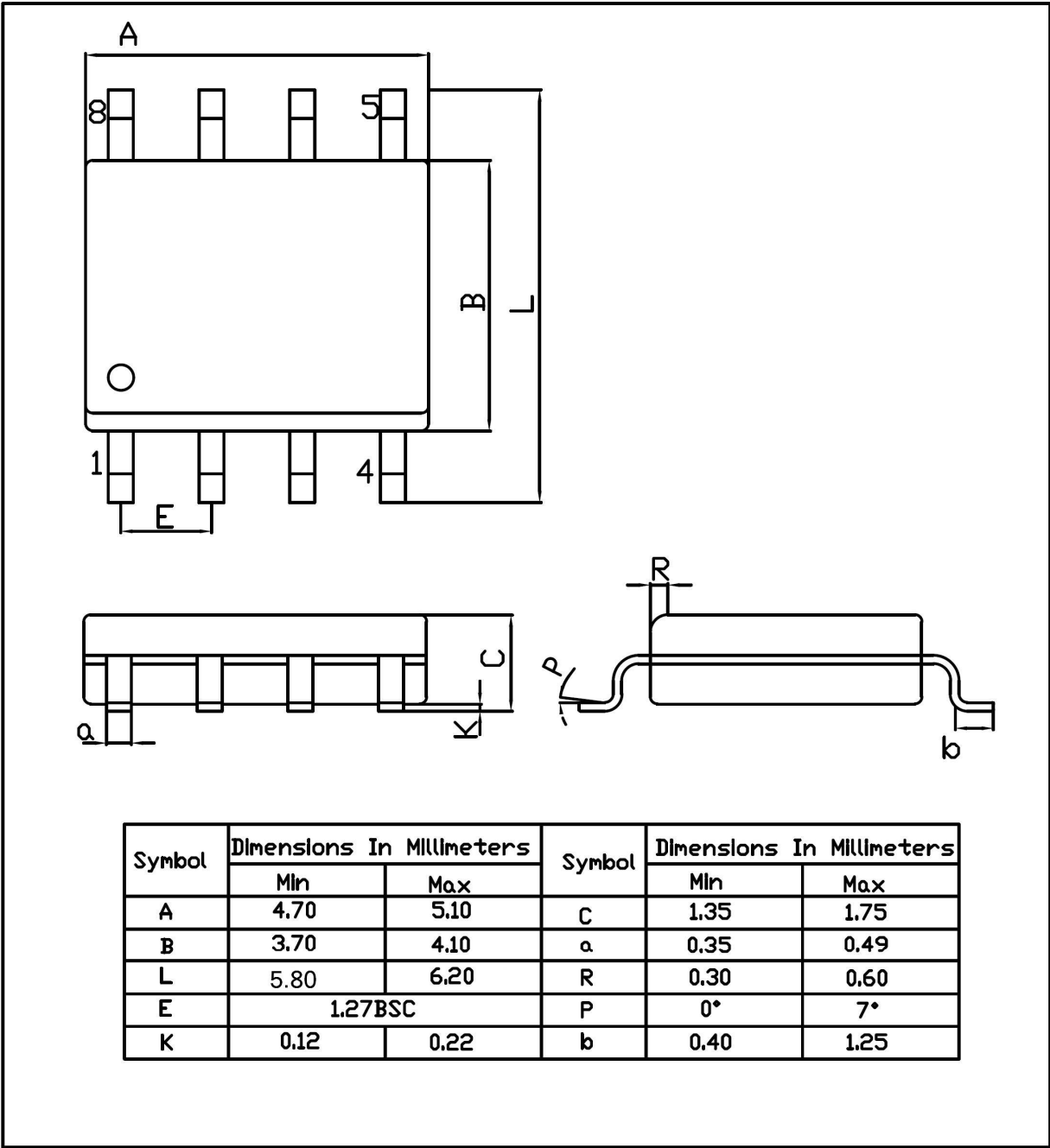


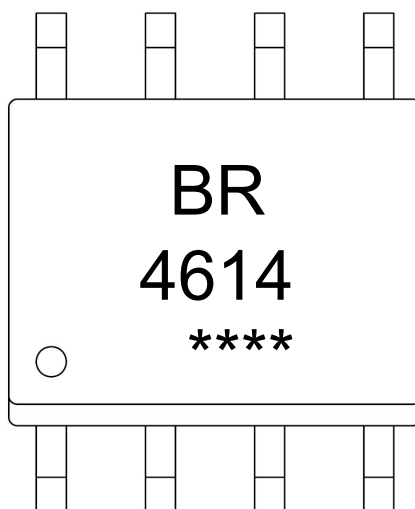
Figure 10: Normalized Maximum Transient Thermal Impedance

外形尺寸图 / Package Dimensions

SOP-8

Unit:mm



**印章说明 / Marking Instructions**

说明：

BR： 为公司代码

4614： 为型号代码

****： 为生产批号代码，随生产批号变化

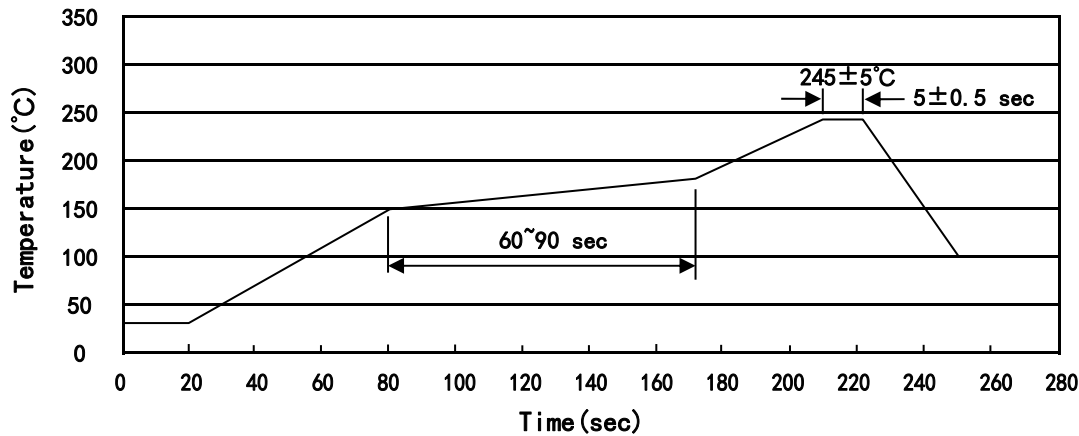
Note:

BR: Company Code

4614: Product Type Code

****: Lot No. Code, code change with Lot No

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)



说明：

- 1、预热温度 150~180°C，时间 60~90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOP/ESOP-8	4,000	2	8,000	6	48,000	13" ×12	360×360×50	380×335×366

使用说明 / Notices